

Silicon NPN Power Transistors

2SD727

DESCRIPTION

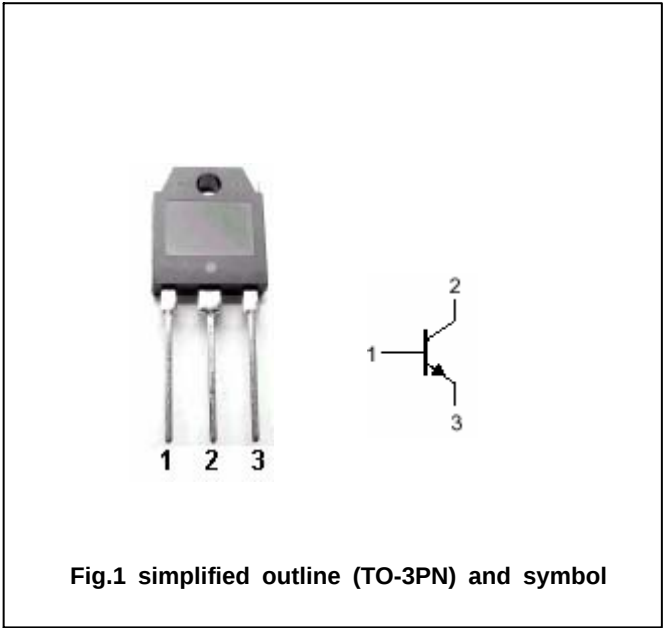
- With TO-3PN package
- Complement to type 2SB691

APPLICATIONS

- For low frequency power amplifier and power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	130	V
V _{CEO}	Collector-emitter voltage	Open base	130	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		5	A
P _C	Collector power dissipation	T _C =25	60	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA ; I_B=0$	130			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A ; I_B=0.5A$			2.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=130V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=1A ; V_{CE}=5V$	60		200	
h_{FE-2}	DC current gain	$I_C=4A ; V_{CE}=5V$	20			
f_T	Transition frequency	$I_C=1A ; V_{CE}=5V$		7		MHz
C_{OB}	Collector output capacitance	$I_E=0 ; f=1MHz ; V_{CB}=10V$		110		pF

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PACKAGE OUTLINE

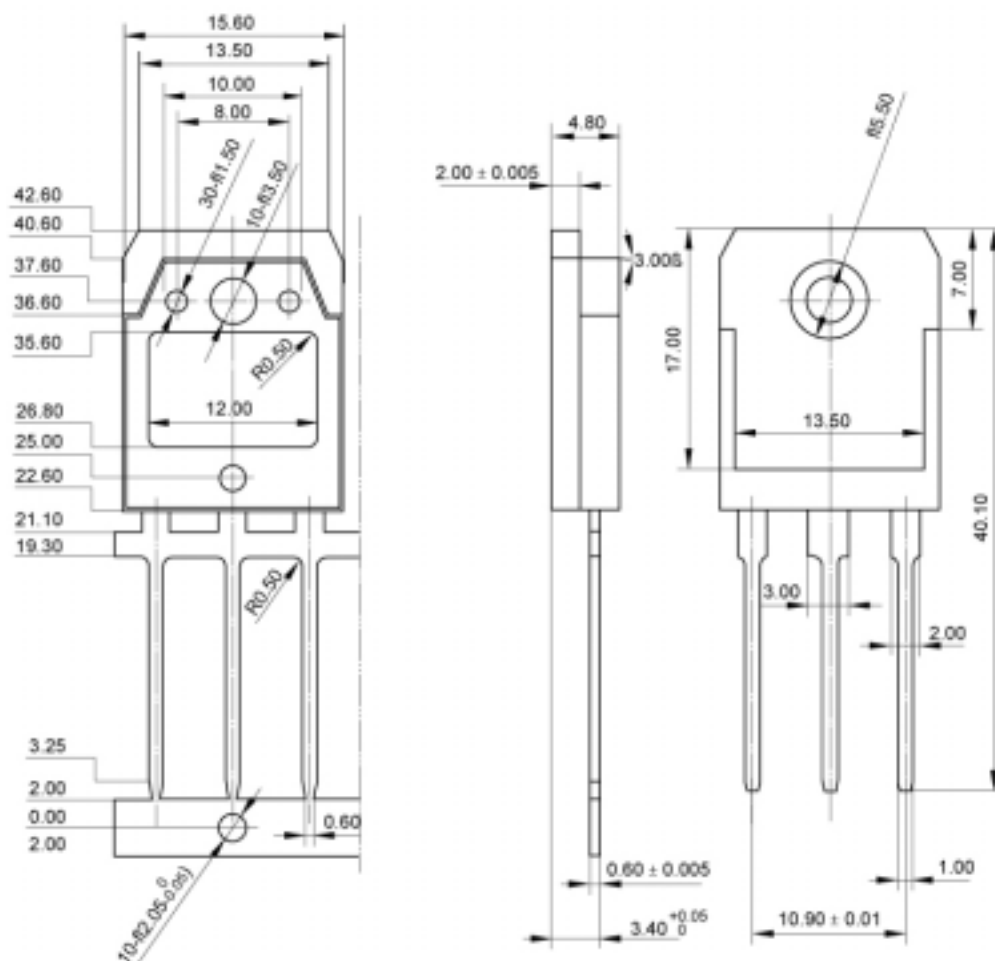


Fig.2 outline dimensions